

Vishay Siliconix

P-Channel 30 V (D-S) MOSFET

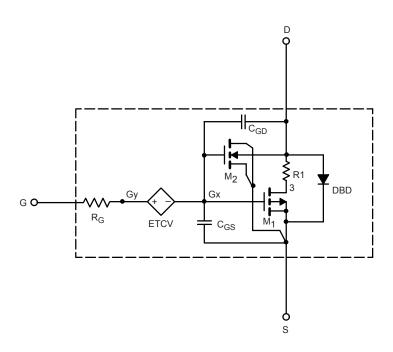
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{\rm gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- · Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 $^{\circ}$ C to + 125 $^{\circ}$ C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

SPICE Device Model Si7145DP

Vishay Siliconix



SPECIFICATIONS T _J = 25 °C, unless otherwise noted					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	1.6	-	٧
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 25 A	0.0021	0.0021	Ω
		V _{GS} = - 4.5 V, I _D = - 20 A	0.0031	0.0030	
Forward Transconductancea	9 _{fs}	V _{DS} = - 15 V, I _D = - 25 A	101	110	S
Diode Forward Voltage ^a	V_{SD}	I _S = - 5 A	- 0.69	- 0.69	V
Dynamic ^b	•				
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz	15 500	15 660	pF
Output Capacitance	C _{oss}		1320	1335	
Reverse Transfer Capacitance	C _{rss}		1540	1570	
Total Gate Charge	Qg	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 20 A	234	275	nC
		V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 20 A	124	129	
Gate-Source Charge	Q _{gs}		37	37	
Gate-Drain Charge	Q _{gd}		40	40	

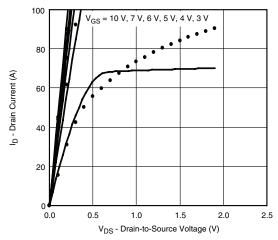
Notes

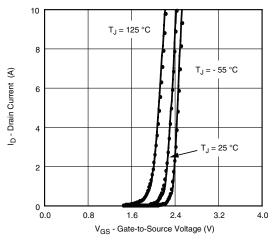
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

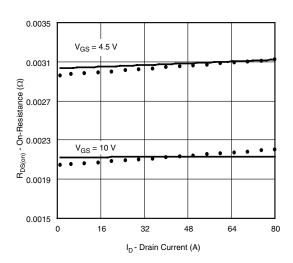


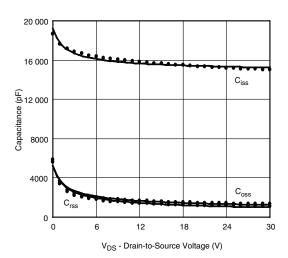
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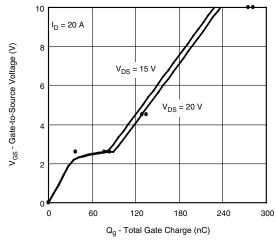
COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25$ °C, unless otherwise noted

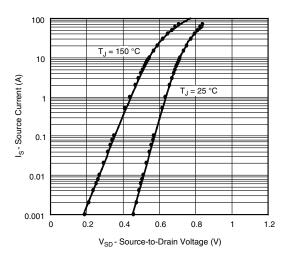












Note

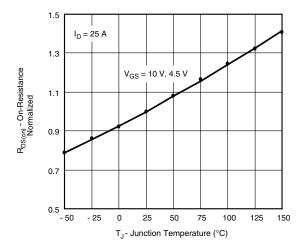
Dots and squares represent measured data.

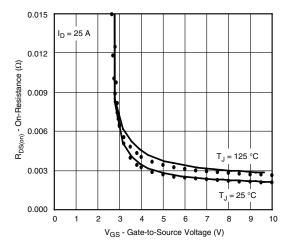
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COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25~{}^{\circ}C$, unless otherwise noted





Note

Dots and squares represent measured data.



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Revision: 18-Jul-08

Document Number: 91000 www.vishay.com